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Performance and Reliability of Deep-Ultraviolet Light-Emitting Diodes Fabricated on AlN Substrates Prepared by Hydride Vapor Phase Epitaxy

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103	High quality semipolar (11 $\bar{0}$ 2) AlGa \bar{N} /AlN quantum wells with remarkably enhanced optical transition probabilities. <i>Applied Physics Letters</i> , 2014 , 104, 252102	3.4	28
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